

Silicon NPN Power Transistor

BU607D

DESCRIPTION

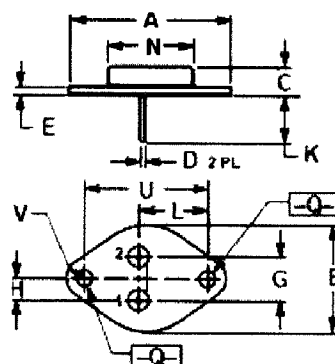
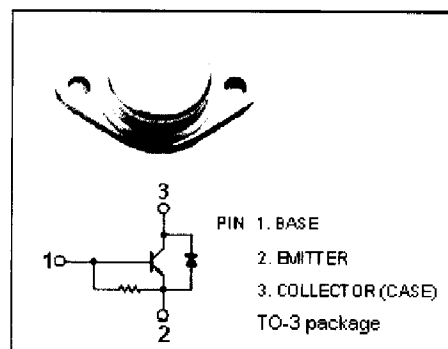
- High Voltage: $V_{CEV} = 330V(\text{Min})$
- Fast Switching Speed-
: $t_r = 0.75 \mu s(\text{Max})$
- Low Saturation Voltage-
: $V_{CE(\text{sat})} = 1.0V(\text{Max}) @ I_C = 5A$

APPLICATIONS

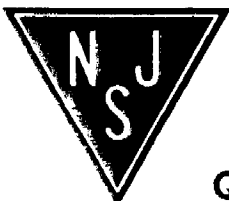
- Designed for use in horizontal deflection output stages of TV's and CRT's

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	330	V
V_{CEV}	Collector-Emitter Voltage	330	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	7	A
I_{CM}	Collector Current-Peak	10	A
I_B	Base Current	4	A
P_C	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	60	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	39.00	
B	25.30	26.67
C	9.30	11.10
D	0.90	1.10
E	2.90	3.10
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50



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ELECTRICAL CHARACTERISTICS

$T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = 100\text{mA}; I_B = 0$	150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 5\text{A}; I_B = 0.65\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 5\text{A}; I_B = 0.65\text{A}$			1.3	V
h_{FE}	DC Current Gain	$I_C = 2\text{A}; V_{CE} = 5\text{V}$		15		
I_{CEV}	Collector Cutoff Current	$V_{CE} = 330\text{V}; V_{BE} = -1.5\text{V}$			15	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 6\text{V}; I_C = 0$			400	mA
f_T	Current-Gain—Bandwidth Product	$I_C = 0.5\text{A}; V_{CE} = 10\text{V}; f_{test} = 1\text{MHz}$	10			MHz
V_{ECF}	C-E Diode Forward Voltage	$I_F = 5\text{A}$			1.5	V
t_f	Fall Time	$I_C = 5\text{A}; I_{B1} = -I_{B2} = 0.65\text{A}; V_{CC} = 40\text{V}$			0.75	μs